

AMENDMENTS TO THE CLAIMS

Claim 1 (Cancelled)

2. (Currently Amended) The method according to claim 14, wherein the first and second portions of the silicon layer initially have the same thickness.

3. (Currently Amended) The method according to claim 14, wherein the step of partially removing the first portion of the silicon layer includes etching the first portion.

4. (Original) The method according to claim 3, wherein the step of partially removing the first portion of the silicon layer includes depositing a resist over the silicon layer and exposing and developing the resist to expose the first portion of the silicon layer.

5. (Original) The method according to claim 3, wherein the thickness of the first portion is determined by etching the first portion for a predetermined length of time.

6. (Currently Amended) The method according to claim 14, wherein the step of partially removing the first portion of the silicon layer includes oxidizing the first portion of the silicon layer and removing the oxidized silicon.

layer and exposing and developing the resist to expose a portion of the mask layer over the first portion of the silicon layer and removing the mask layer over the first portion of the silicon layer.

8. (Original) The method according to claim 7, further comprising the step of removing the mask layer.

9. (Original) The method according to claim 7, wherein the mask layer is an antireflective material.

10. (Previously Amended) The method according to claim 7, wherein the mask layer is silicon nitride.

11. (Currently Amended) The method according to claim 14, wherein isolating features are formed before the first portion of the silicon layer is partially removed.

12. (Currently Amended) The method according to claim 14, wherein isolating features are formed after the first portion of the silicon layer is partially removed.

13. (Cancelled)

14. (Currently Amended) ~~The~~ A method according to claim 13 of manufacturing a

providing a silicon layer over an insulating layer, the silicon layer including a first portion and a second portion;

partially removing the first portion of the silicon layer, wherein a thickness of the second portion is greater than a thickness of the first portion; and

forming a first transistor in the first portion and a second transistor in the second portion,
wherein

the first transistor includes first source/drain regions and the second transistor includes second source/drain regions ~~formed~~, and a depth of the second source/drain regions greater than a depth of the first source/drain regions.

15. (Currently Amended) The method according to claim 14 ~~43~~, wherein the first transistor ~~includes~~ source/drain regions are formed with a first dopant and the second transistor ~~includes~~ source/drain regions are formed with a second dopant, and the diffusivity of the second dopant into silicon is greater than the diffusivity of the first dopant into silicon.

16. (Currently Amended) A semiconductor device, comprising:
an insulating layer;
a silicon layer over the insulating layer, the silicon layer including a first portion and a second portion; and
a first transistor is formed in the first portion and a second transistor is formed in the second portion,

second source drain regions, and a depth of the second source drain regions greater than a depth of the first source drain regions.

Claim 17 (Cancelled)

18. (Original) The semiconductor device according to claim 16 ~~47~~, wherein the first transistor includes source/drain regions formed with a first dopant and the second transistor includes source/drain regions formed with a second dopant, and the diffusivity of the second dopant into silicon is greater than the diffusivity of the first dopant into silicon.

19. (Currently Amended) The semiconductor device according to claim 16 ~~47~~, wherein the first transistor includes source/drain regions ~~formed with a first dopant~~ and the second transistor includes source/drain regions do not extend to the insulating layer formed with a second dopant, and the diffusivity of the second dopant into silicon is greater than the diffusivity of the first dopant into silicon.

20. (New) The semiconductor device according to claim 14, wherein the first source drain regions and the second source drain regions do not extend to the insulating layer.